



Europe TC Chapter Compound Semiconductor Materials Global Technical Committee

Liaison Report

November 2024

v1

STANDARDS

Meeting Information

- Last meeting
 - November 14, 2024
 - SEMICON Europa
 - Munich, Germany
- Next meeting
 - Virtual meeting in Spring 2025
 - In-Person during SEMICON Europa 2025

<http://www.semi.org/en/standards-events>

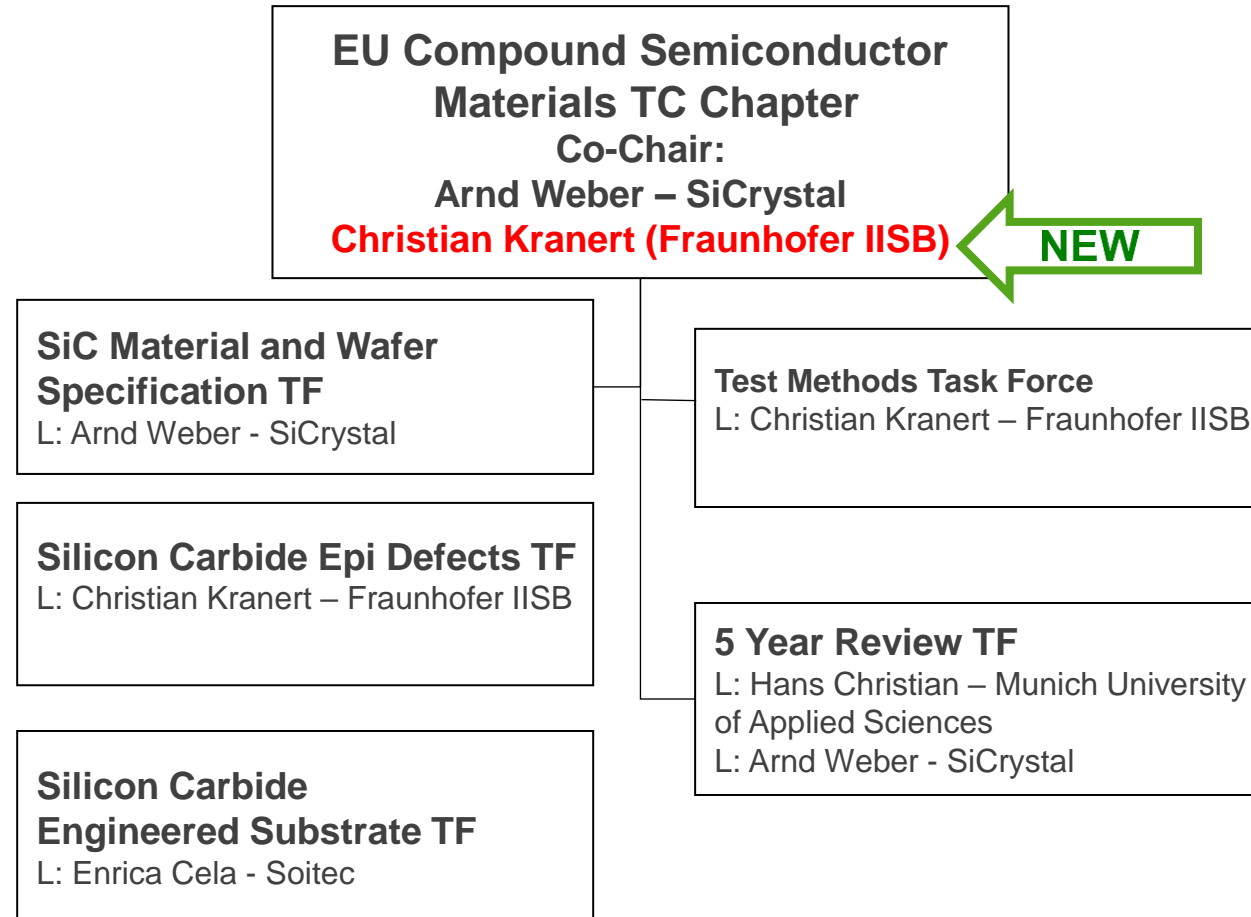
Leadership

- Co-Chair: Arnd Weber (SiCrystal)



- Newly appointed chair at SEMICON Europa 2024
 - Christian Kranert (Fraunhofer IISB)

Organization Chart



Ballot Result

- Doc. 7225, New Standard: Specification for Silicon Carbide Engineered Substrate
 - Passed, with technical changes and with or without editorial changes
 - Ratification Ballot to be issued

Task Force Highlights [1/3]

- Silicon Carbide Epi Defects TF
 - Leader - Christian Kranert (Fraunhofer IISB)
 - 7160, New Standard: Guide for Defects found in Homoepitaxial Layers of Silicon Carbide
 - Ongoing, plan to have something ready by Spring meetings in 2025
- Silicon Carbide Engineered Substrate TF
 - Leader - Enrica Cela (Soitec)
 - Ballot Review for 7225, New standard: Specification for Silicon Carbide Engineered Substrate
 - Passed, with technical changes and with or without editorial changes
 - Ratification Ballot to be issued

Task Force Highlights [2/3]

- SiC Material and Wafer Specification TF
 - Leader: Arnd Weber (SiCrystal)
 - Drafting Doc. 7111, Revision of SEMI M81-0418, Guide to Defects Found in Monocrystalline Silicon Carbide Substrates
 - Extended SNARF one-year to November 2025
- Test Methods TF
 - Leader: Christian Kranert (Fraunhofer)
 - 7161, Line-Item Revision of SEMI M93-0923 Test Method for Quantifying Basal Plane Dislocation Density in 4H-SiC by X-Ray Diffraction Topography/Imaging
 - Published June 2024

Task Force Highlights [3/3]

- 5 Year Review TF
 - Leaders
 - Hans Christian – Munich University of Applied Sciences
 - Arnd Weber (SiCrystal)
 - Reviewing Standards due for 5-year review
 - 7233, SEMI M54-0319 - Guide for Semi-Insulating (SI) GaAs Material Parameters
 - Published in September 2024
 - 7280, SEMI M83-0820 - Test Method for Determination of Dislocation Etch Pit Density in Monocrystals of III-V Compound Semiconductors
 - Drafting; authorized for ballot early possible cycle next year, 2025.



THANK YOU

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STANDARDS